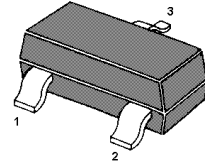


MMBTSA1576

PNP Silicon Epitaxial Planar Transistor

The transistor is subdivided into three groups Q, R and S according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1.BASE 2.EMITTER 3.COLLECTOR

Feature

- Excellent h_{FE} linearity

SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	150	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	-55 to +150	$^\circ\text{C}$

TOP DYNAMIC

MMBTSA1576

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE}=6\text{V}$, $-I_C=1\text{mA}$	Q	h_{FE}	120	-	270	-
	R	h_{FE}	180	-	390	-
	S	h_{FE}	270	-	560	-
Collector Cutoff Current at $-V_{CB}=60\text{V}$		$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current at $-V_{EB}=6\text{V}$		$-I_{EBO}$	-	-	0.1	μA
Collector Saturation Voltage at $-I_C=50\text{mA}$, $-I_B=5\text{mA}$		$-V_{CE(sat)}$	-	-	0.5	V
Collector Base Breakdown Voltage at $-I_C=50\mu\text{A}$		$-V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $-I_C=1\text{mA}$		$-V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $-I_E=50\mu\text{A}$		$-V_{(BR)EBO}$	6	-	-	V
Transition Frequency at $-V_{CE}=12\text{V}$, $-I_E=2\text{mA}$, $f=30\text{MHz}$		f_T	-	140	-	MHz
Output Capacitance at $-V_{CB}=12\text{V}$, $f=1\text{MHz}$		Cob	-	4.0	5	pF

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